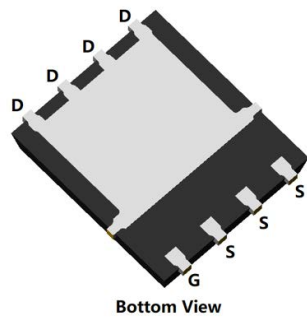
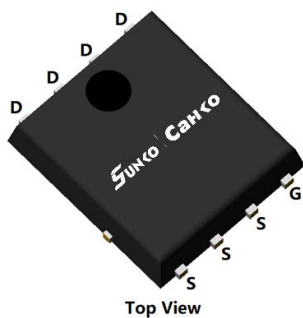
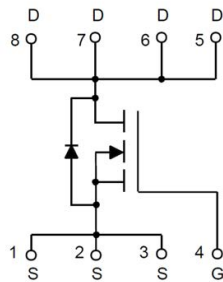


P-Channel Enhancement Mode Field Effect Transistor



PDFN5060-8L



Product Summary

- V_{DS} -80 V
- I_D -50 A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) <17 m Ω
- $R_{DS(ON)}$ (at $V_{GS}=-6V$) <19 m Ω
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) <22 m Ω
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- Low $R_{DS(on)}$ & FOM
- Excellent stability and uniformity
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power management
- Portable equipment

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-80	V
Gate-source Voltage		V_{GS}	± 18	V
Drain Current	$T_A=25^\circ\text{C}$	I_D	-8	A
	$T_A=100^\circ\text{C}$		-5	
	$T_C=25^\circ\text{C}$		-50	
	$T_C=100^\circ\text{C}$		-31	
Pulsed Drain Current ^A		I_{DM}	-200	A
Avalanche energy ^B		EAS	600	mJ
Total Power Dissipation ^C	$T_A=25^\circ\text{C}$	P_D	2.5	W
	$T_A=100^\circ\text{C}$		1	
	$T_C=25^\circ\text{C}$		104	
	$T_C=100^\circ\text{C}$		41	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	40	50	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1	1.2	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SCG50GP08A	F1	SCG50GP08A	5000	10000	100000	13" reel

SCG50GP08A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA	-80	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-80V, V _{GS} =0V	-	-	-1	μA
		V _{DS} =-80V, V _{GS} =0V, T _j =150°C	-	-	-100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±18V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250μA	-1.2	-2.1	-3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-25A	-	13.5	17	mΩ
		V _{GS} =-6V, I _D =-20A	-	14.5	19	
		V _{GS} =-4.5V, I _D =-20A	-	16	22	
Diode Forward Voltage	V _{SD}	I _S =-25A, V _{GS} =0V	-	-0.85	-1.2	V
Gate resistance	R _G	f=1MHz	-	8	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	-50	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-40V, V _{GS} =0V, f=1MHz	-	5330	-	pF
Output Capacitance	C _{oss}		-	490	-	
Reverse Transfer Capacitance	C _{rss}		-	45	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-40V, I _D =-25A	-	93	-	nC
Gate-Source Charge	Q _{gs}		-	25	-	
Gate-Drain Charge	Q _{gd}		-	16	-	
Reverse Recovery Charge	Q _{rr}	I _F =-25A, di/dt=100A/us	-	124	-	nC
Reverse Recovery Time	t _{rr}		-	63	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DD} =-40V, ID=-25A R _{GEN} =3Ω	-	14	-	ns
Turn-on Rise Time	t _r		-	81	-	
Turn-off Delay Time	t _{D(off)}		-	137	-	
Turn-off fall Time	t _f		-	84	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_{DD}=-50V, V_G=-10V, R_G=25Ω, L=3mH, I_{AS}=-20A.

C. P_d is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.

D. The value of RθJA is measured with the device mounted on the minimum recommend pad size, in the still air environment with T_A =25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

■ Typical Electrical and Thermal Characteristics Diagrams

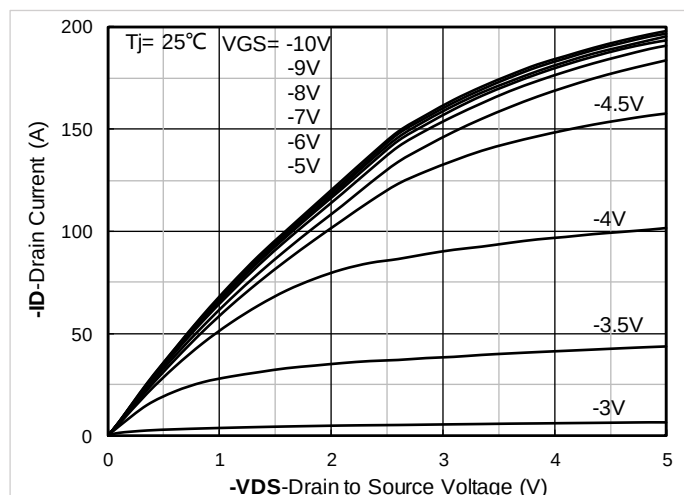


Figure 1. Output Characteristics

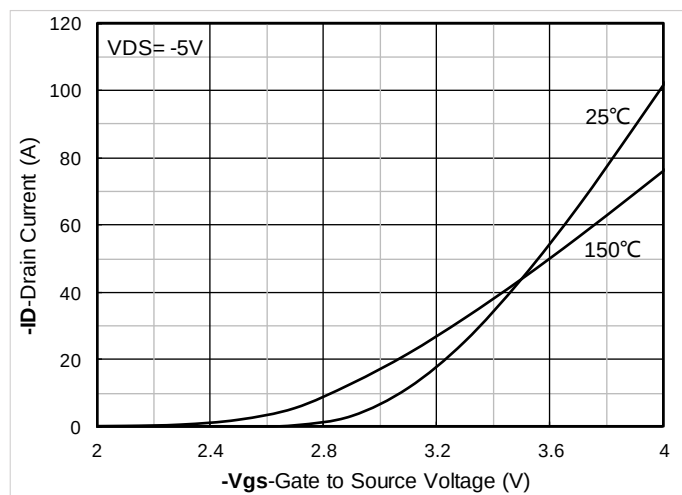


Figure 2. Transfer Characteristics

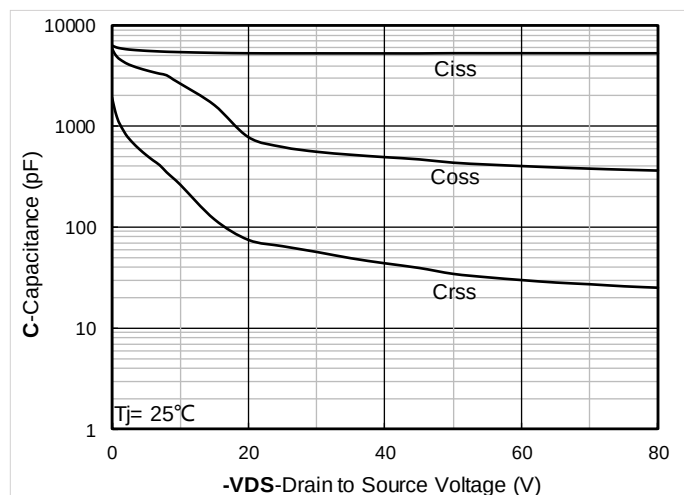


Figure 3. Capacitance Characteristics

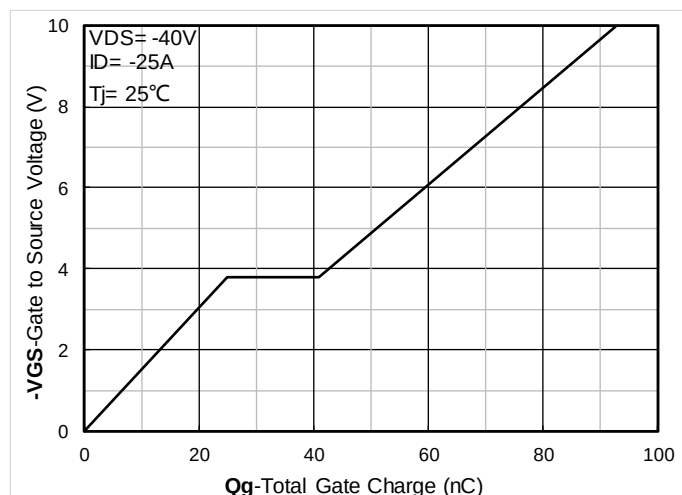


Figure 4. Gate Charge

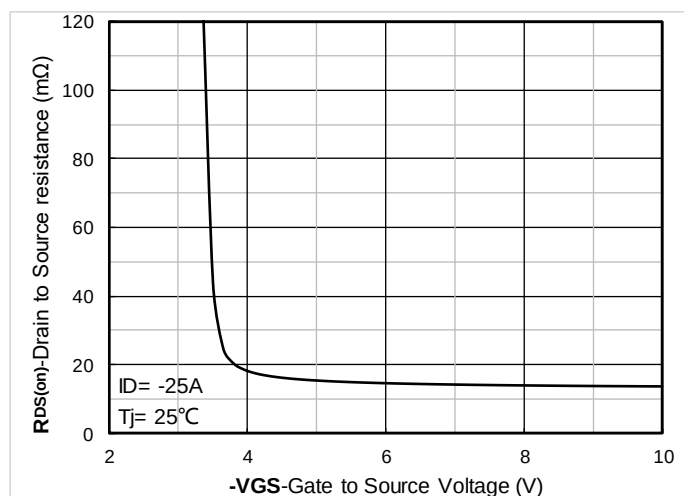


Figure 5. On-Resistance vs Gate to Source Voltage

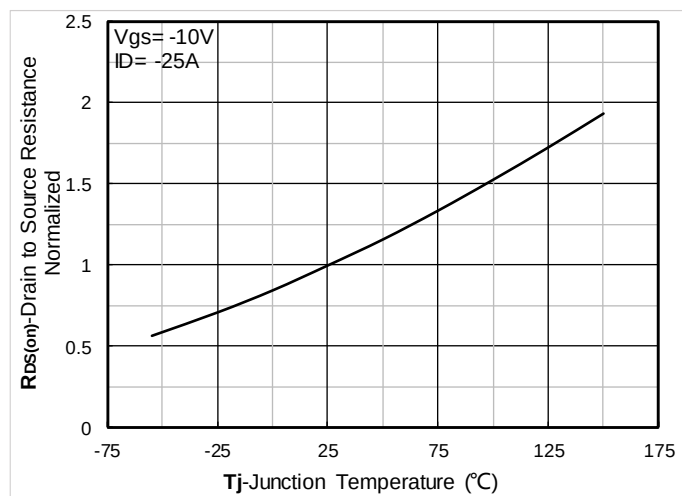


Figure 6. Normalized On-Resistance

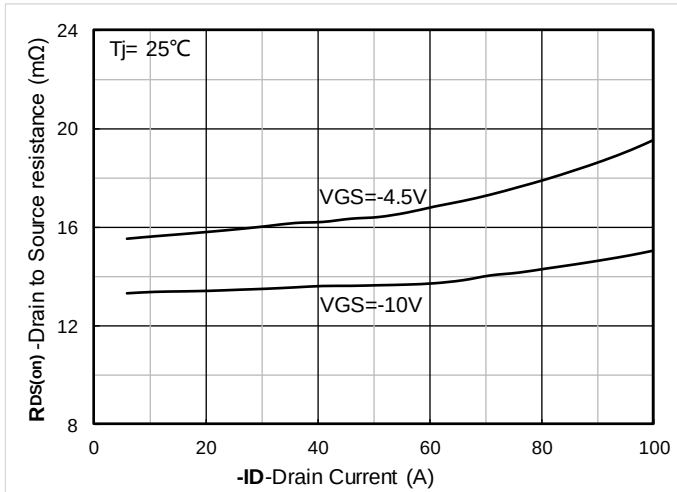


Figure 7. $R_{DS(on)}$ VS Drain Current

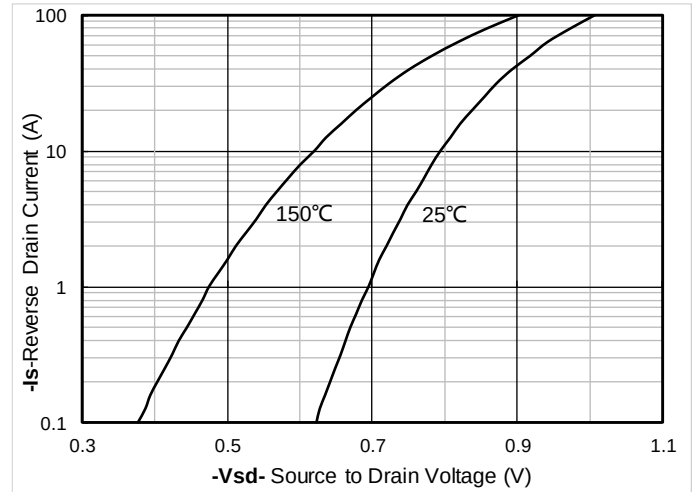


Figure 8. Forward characteristics of reverse diode

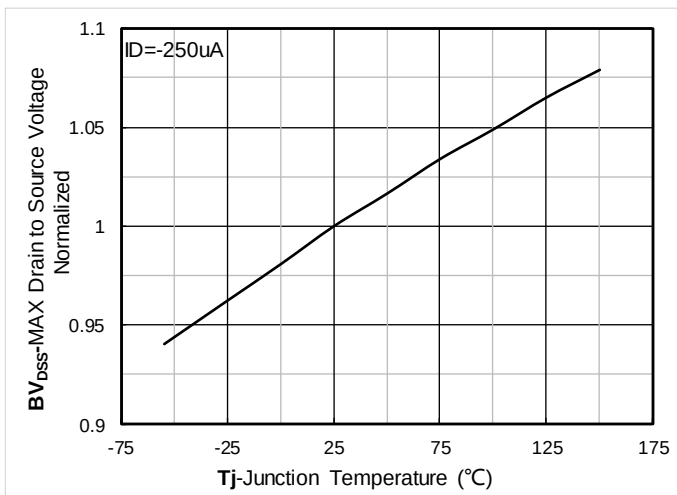


Figure 9. Normalized breakdown voltage

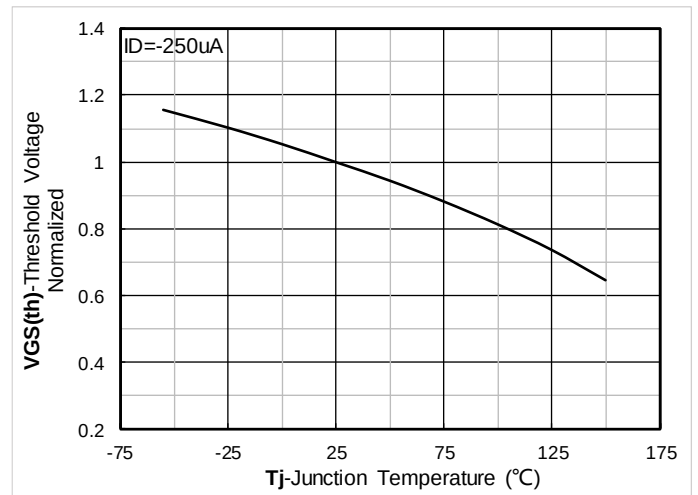


Figure 10. Normalized Threshold voltage

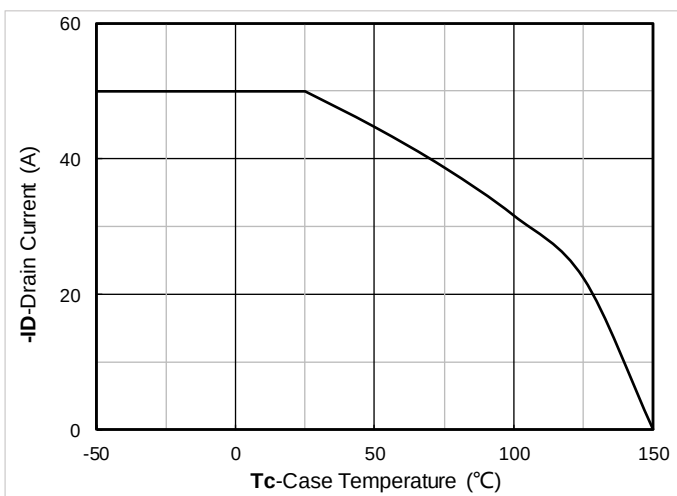


Figure 11. Current dissipation

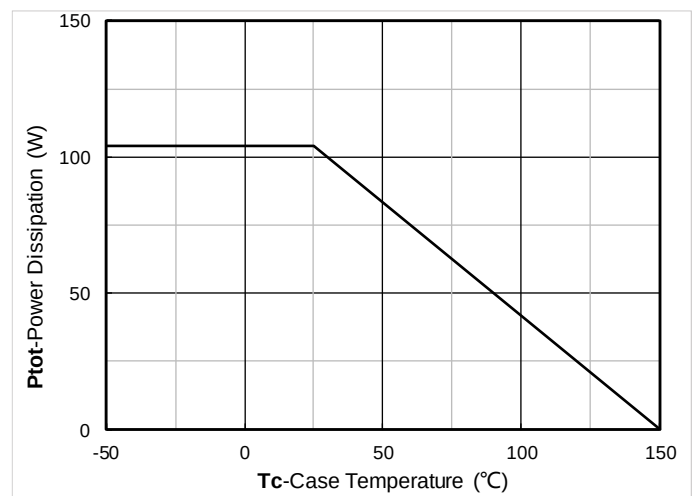


Figure 12. Power dissipation

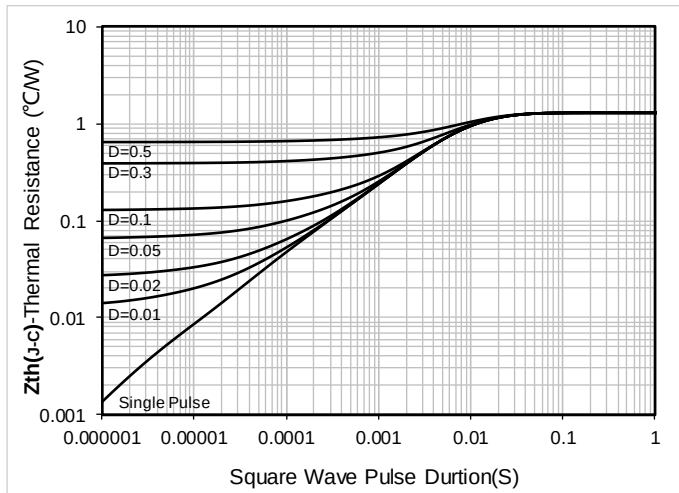


Figure 13. Maximum Transient Thermal Impedance

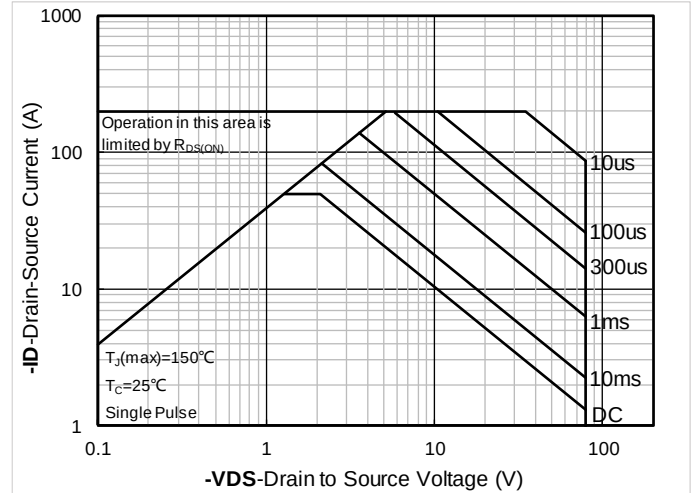
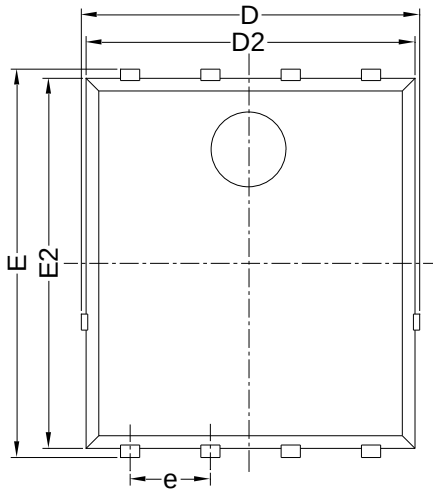
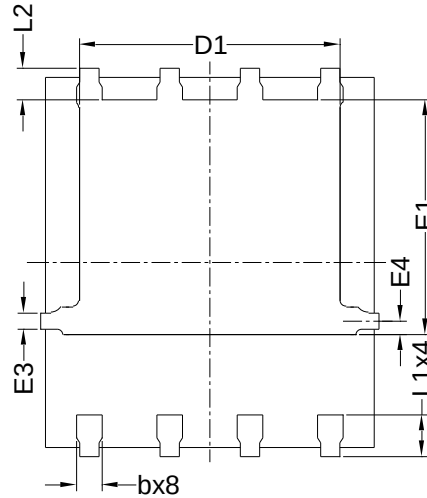


Figure 14. Safe Operation Area

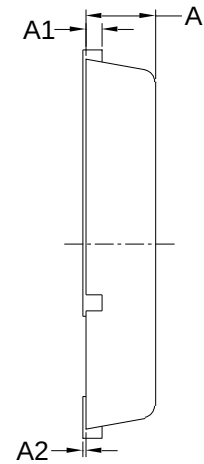
■ PDFN5060-8L-B-1.1MM Package information



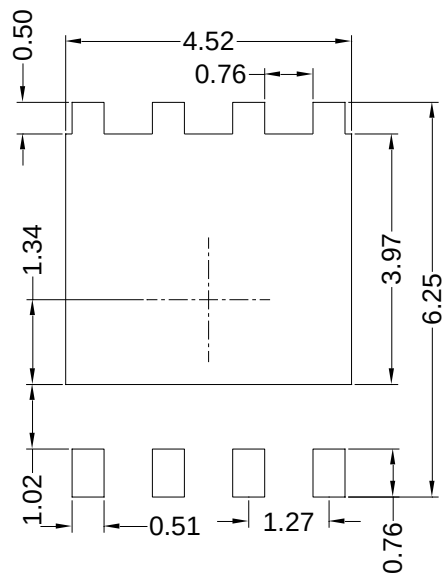
Top View
正面视图



Bottom View
背面视图



Side View
侧面视图



Suggested Solder Pad Layout
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.

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